IFW

Attorney Docket: BHT/3230-86

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	:	WU
Application No.	:	10/781,892
Filed	:	February 20, 2004
Title	:	METHOD FOR LIFT OFF GaN PSEUDOMASK EPITAXY LAYER USING WAFER BONDING WAY
Group Art Unit	:	2811
Examiner	:	Unassigned
Docket No.	:	BHT/3230-86

OFFICE OF INITIAL PATENT EXAMINATION
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

TRANSMITTAL COVER SHEET

Sir:

Transmitted herewith for filing are the following:
1. INFORMATION DISCLOSURE STATEMENT.
2. Form PTO-1449 (in duplicate), along with copies of the eight (8) articles cited therein.

The Commissioner is hereby authorized to charge any fees which may be required for the filing of this document to **Deposit Account No. 501874**

Respectfully submitted,

Date: June 9, 2004 By: _____
Bruce H. Troxell
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INFORMATION DISCLOSURE STATEMENT

Sir:

In compliance with the duty of disclosure under 37 CFR 1.56, and 37 CFR 1.97-1.98, the documents listed on the attached form PTO-1449 are hereby made of record in this patent application. Copies of the listed documents, excluding any U.S. patent/publication references, are enclosed.

As this Information Disclosure Statement is being filed prior to the mailing of the first Official Action in this application, no fee is believed due in order to have the enclosed references considered by the Examiner and made of record in the application.

Early action on the merits of the application is earnestly solicited.

Respectfully submitted,

Date: June 9, 2004 By: _____

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FORM PTO 1449 (modified)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

LIST OF REFERENCES CITED BY APPLICANT(S)
(Use several sheets if necessary)

Date Submitted to PTO: **JUNE 9, 2004**

ATTY DOCKET NO. **3230-86**	APPLICATION NO. **10/781,892**
APPLICANT **WU et al.**	
FILING DATE **February 20, 2004**	GROUP **2811**

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

		Y. Honda et al.; "Selective Area Growth Of GaN Microstructure On Patterned (111) and (001) Si Substrates"; *Journal of Crystal Growth 230";* pp. 346-350; 2001
		B. Beaumont et al; "Lateral Overgrowth Of GaN On Patterned GaN/Sapphire Substrate Via Selective Metal Organic Vapour Phase Epitaxy: A Route to Produce Self Supported GaN Substrates"; *Journal of Crystal Growth 189/190"' pp. 97-102; 1998*
		Jaime A. Freitas, et al.; "Optical And Structural Properties Of Lateral Epitaxial Overgrown GaN Layers"; *Journal of Crystal Growth 189/190*; pp. 92-96; 1998
		Shuji Nakamura et al.; "Present Status Of InGaN/GaN/AlGaN-based Laser Diodes"; *Journal of Crystal Growth 189/190*; pp. 820-825; 1998
		Kazumasa Hiramatsu et al; "Selective Area Growth And Epitaxial Lateral Overgrowth of GaN by Metalorganic Vapor Phase Epitaxy and Hydride Vapor Phase Epitaxy"; *Materials Science and Engineering B59*; pp. 104-111; 1999
		Tsvetanka S. Zheleva, et al.; "Lateral Epitaxy and Dislocation Density Reduction in Selectively Grown GaN Structures"; *Journal of Crystal Growth 222*; pp. 706-718; 2001
		W. S. Wong et al.; "In $XGa_{1-x}N$ Light Emitting Diodes on Si Substrates Fabricated by Pd-In Metal Bonding and Laser Lift-off"; *Applied Physics Letters Volume 77; Number 18*;pp. 2822-2824; 2000
		Mitsuru Funato et al.; "Integration of GaN With Si Using a AuGe-Mediated Wafer Bonding Technique"; *Applied Physics Letters Volume 77; Number 24*; pp. 3959-3961; 2000

EXAMINER	DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.